

Features

- 650-Volt Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

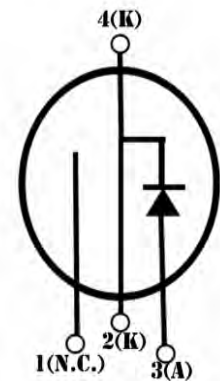
Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters

Package



Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	650	V		
V_{RSM}	Surge Peak Reverse Voltage	650	V		
V_{DC}	DC Blocking Voltage	650	V		
I_F	Continuous Forward Current	20 10 8	A	$T_C=25^\circ\text{C}$ $T_C=130^\circ\text{C}$ $T_C=140^\circ\text{C}$	Fig. 3
I_{FRM}	Repetitive Peak Forward Surge Current	36.5 25.5	A	$T_C=25^\circ\text{C}$, $t_p = 10$ ms, Half Sine Wave $T_C=100^\circ\text{C}$, $t_p = 10$ ms, Half Sine Wave	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	71 60	A	$T_C=25^\circ\text{C}$, $t_p = 10$ ms, Half Sine Wave $T_C=100^\circ\text{C}$, $t_p = 10$ ms, Half Sine Wave	Fig. 8
I_{FSM}	Non-Repetitive Peak Forward Surge Current	650 530	A	$T_C=25^\circ\text{C}$, $t_p = 10$ μs , Pulse $T_C=100^\circ\text{C}$, $t_p = 10$ μs , Pulse	Fig. 8
P_{tot}	Power Dissipation	107 46.5	W	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	$V_R=0-650\text{V}$	
$\int i^2 dt$	i^2t value	25 18	A^2s	$T_C=25^\circ\text{C}$, $t_p=10$ ms $T_C=100^\circ\text{C}$, $t_p=10$ ms	
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 2.1	1.8 2.4	V	$I_F = 8\text{ A } T_J = 25^\circ\text{C}$ $I_F = 8\text{ A } T_J = 175^\circ\text{C}$	Fig. 1
I_R	Reverse Current	8.5 17	42.5 170	μA	$V_R = 650\text{ V } T_J = 25^\circ\text{C}$ $V_R = 650\text{ V } T_J = 175^\circ\text{C}$	Fig. 2
Q_C	Total Capacitive Charge	20		nC	$V_R = 400\text{ V}, I_F = 8\text{ A}$ $di/dt = 500\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	Fig. 5
C	Total Capacitance	395 37 32		pF	$V_R = 0\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$ $V_R = 200\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$ $V_R = 400\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$	Fig. 6
E_C	Capacitance Stored Energy	3.0		μJ	$V_R = 400\text{ V}$	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.4	$^\circ\text{C}/\text{W}$	Fig. 9

Typical Performance

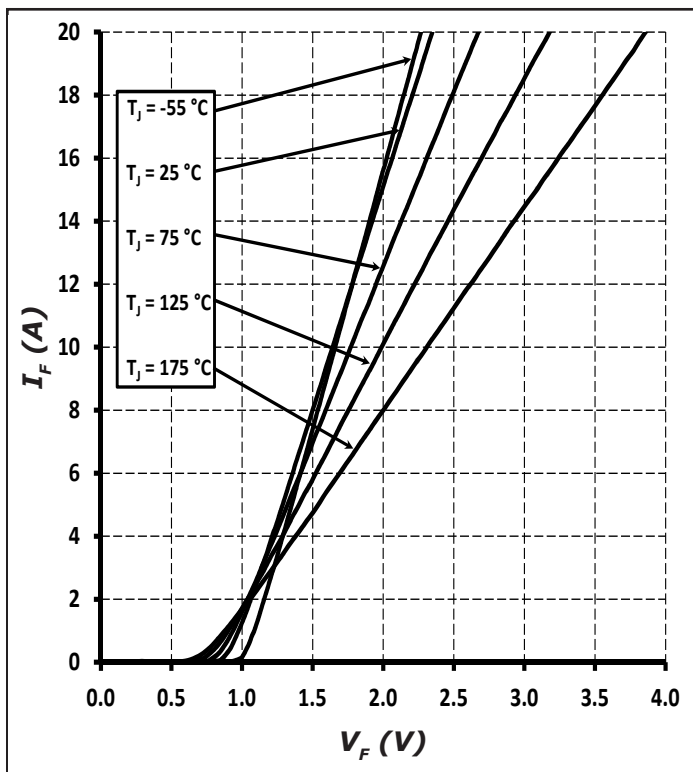


Figure 1. Forward Characteristics

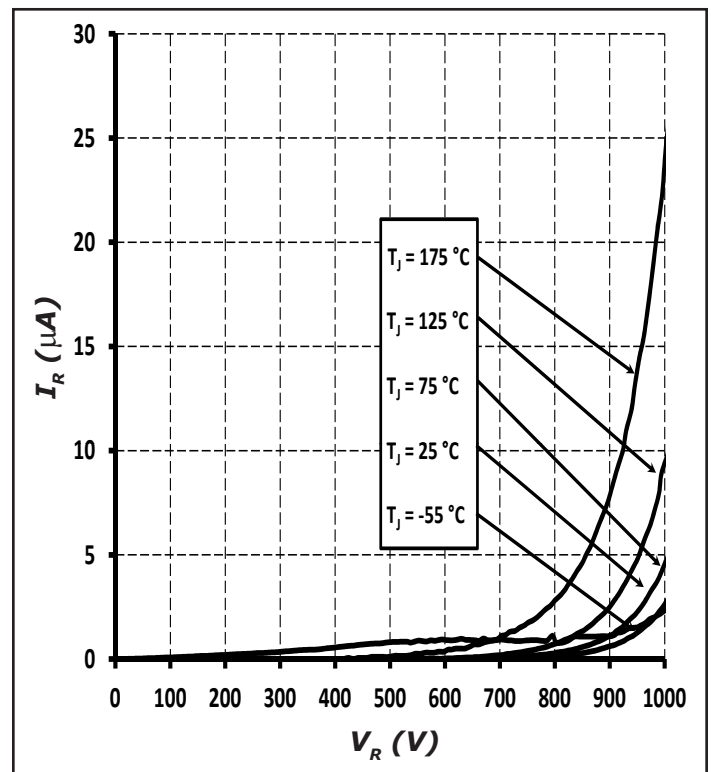


Figure 2. Reverse Characteristics

Typical Performance

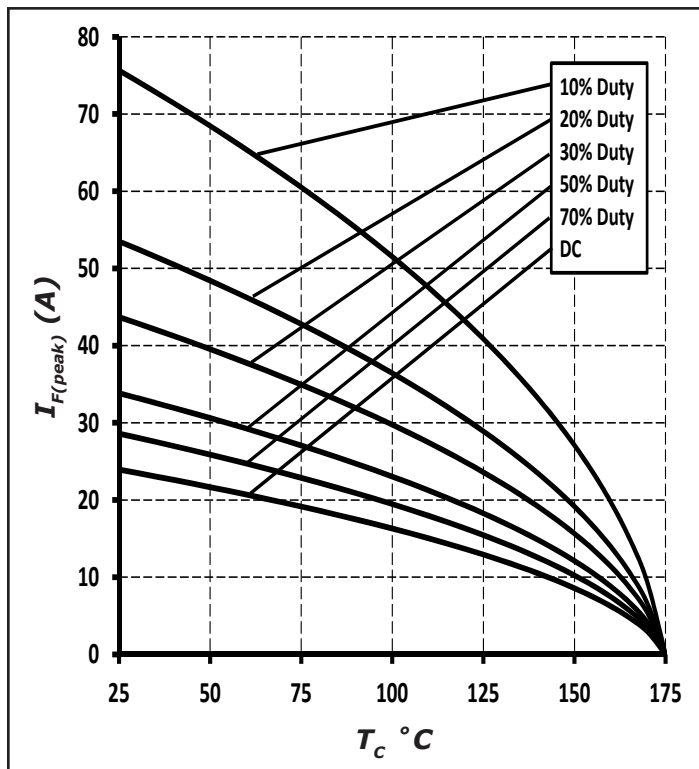


Figure 3. Current Derating

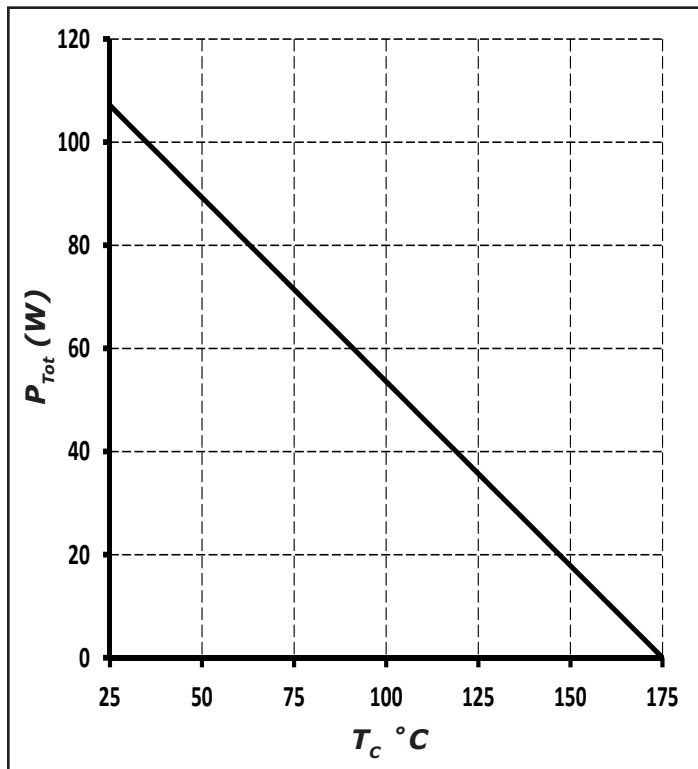


Figure 4. Power Derating

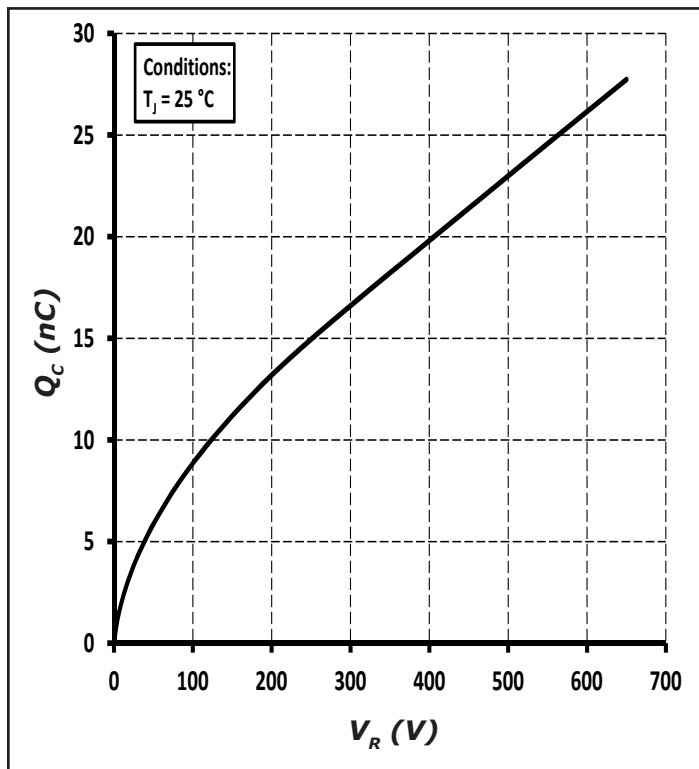


Figure 5. Total Capacitance Charge vs. Reverse Voltage

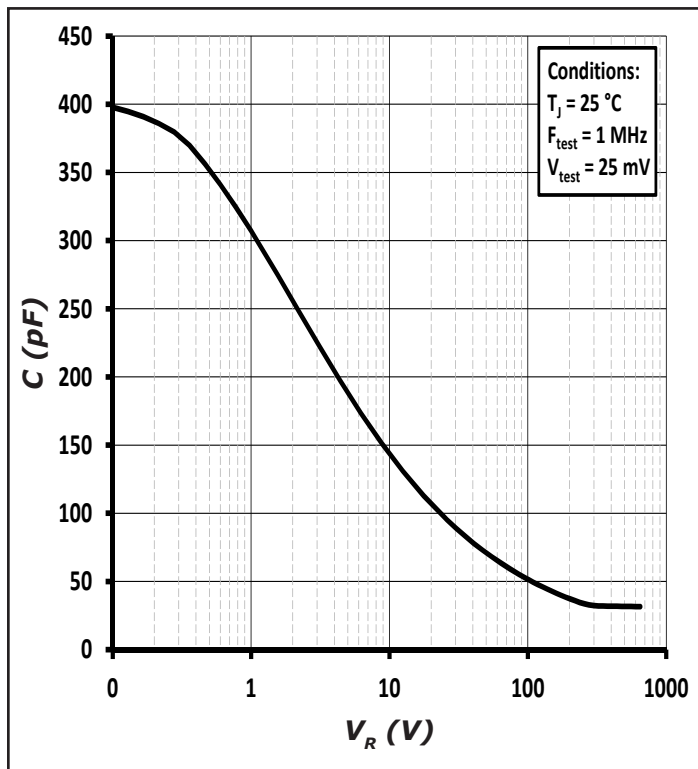


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance

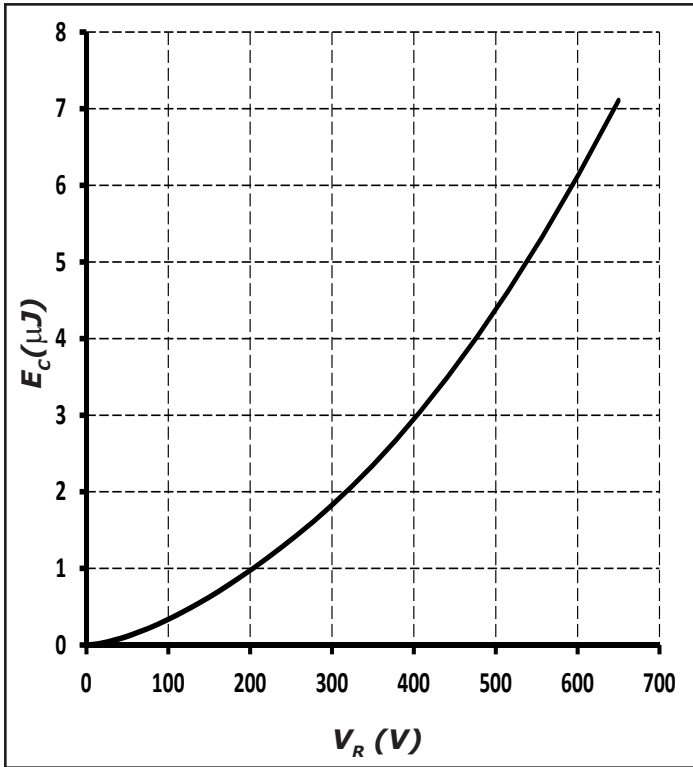


Figure 7. Capacitance Stored Energy

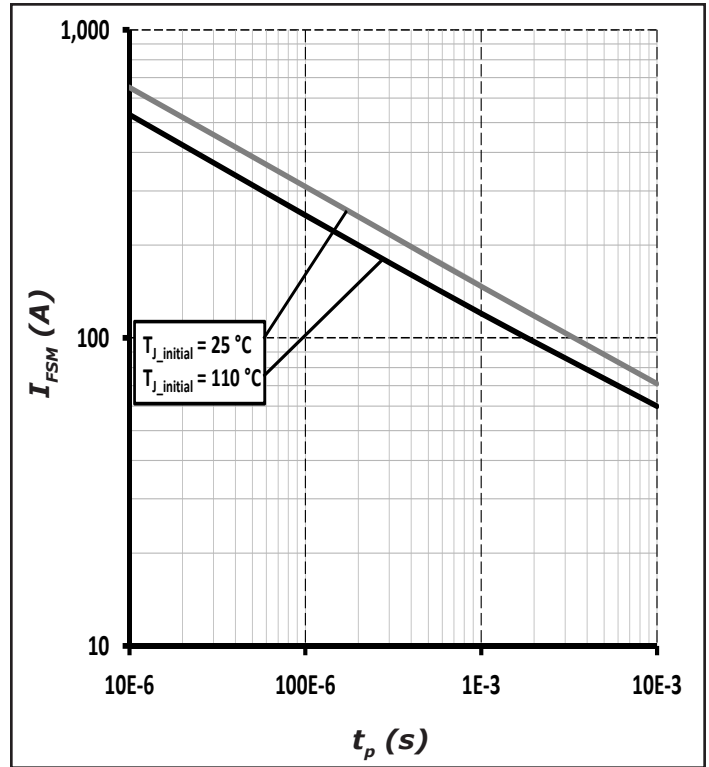


Figure 8. Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

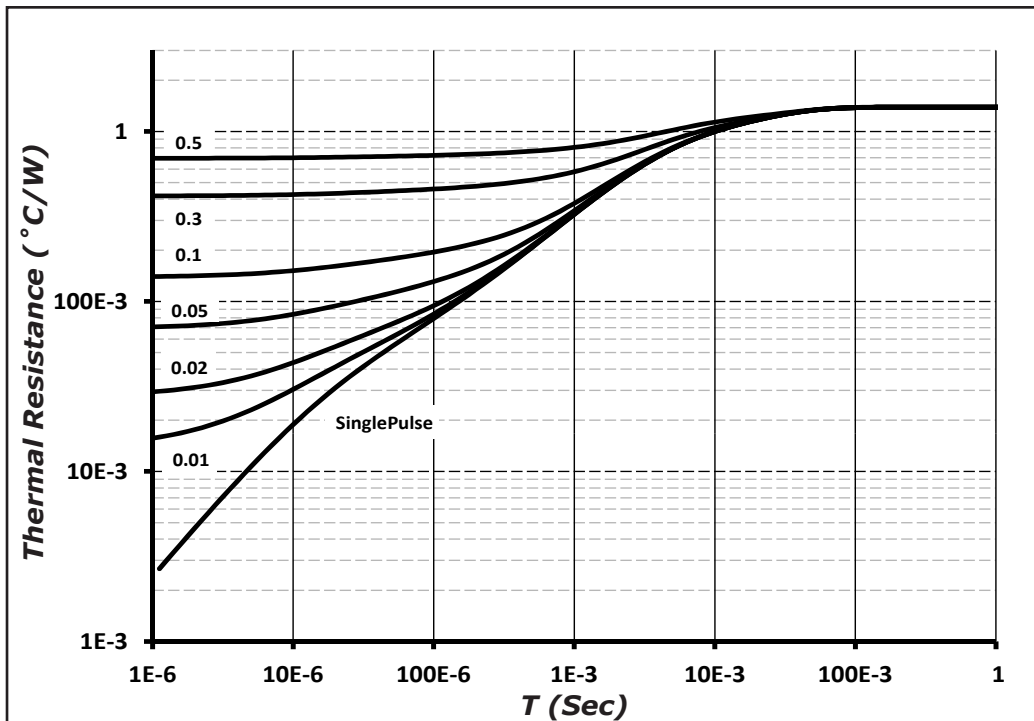
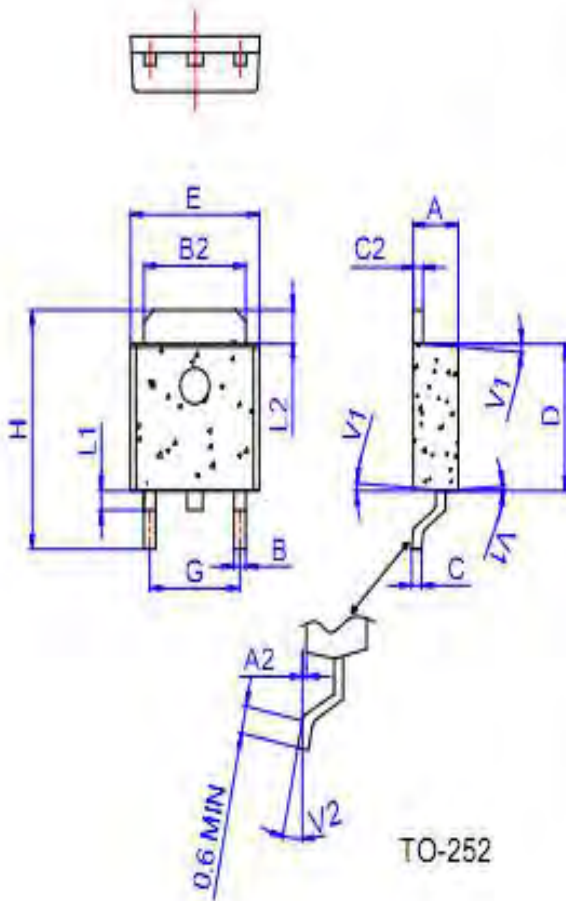


Figure 9. Transient Thermal Impedance

Package Dimensions



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2	0°		8°	0°		8°